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| SANYO | No.4411 | 2SC4910 |
| | | NPN Epitaxial Planar Silicon Transistor |

VHF-Band Power Amp Applications

Features

- On-chip emitter ballast resistors.

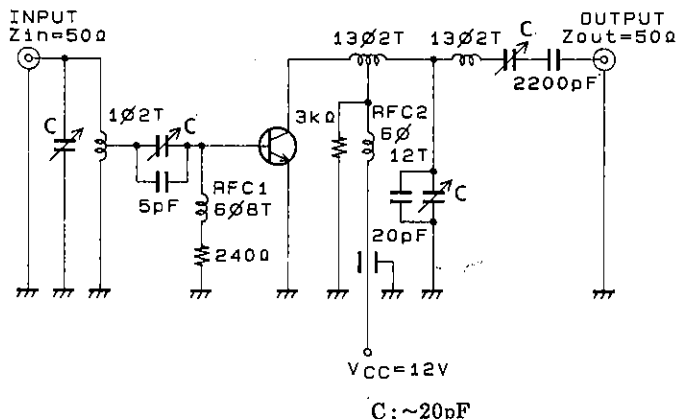
Absolute Maximum Ratings at Ta = 25°C

| | | | unit |
|------------------------------|------------------|-------------|------|
| Collector-to-Base Voltage | V _{CB0} | 38 | V |
| Collector-to-Emitter Voltage | V _{CE0} | 18 | V |
| Emitter-to-Base Voltage | V _{EBO} | 3 | V |
| Collector Current | I _C | 0.75 | A |
| Collector Current (Pulse) | I _{CP} | 1.2 | A |
| Base Current | I _B | 150 | mA |
| Collector Dissipation | P _C | 1.5 | W |
| Junction Temperature | T _j | 150 | °C |
| Storage Temperature | T _{stg} | -55 to +150 | °C |

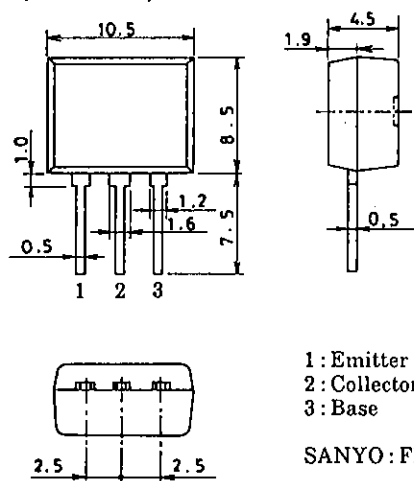
Electrical Characteristics at Ta = 25°C

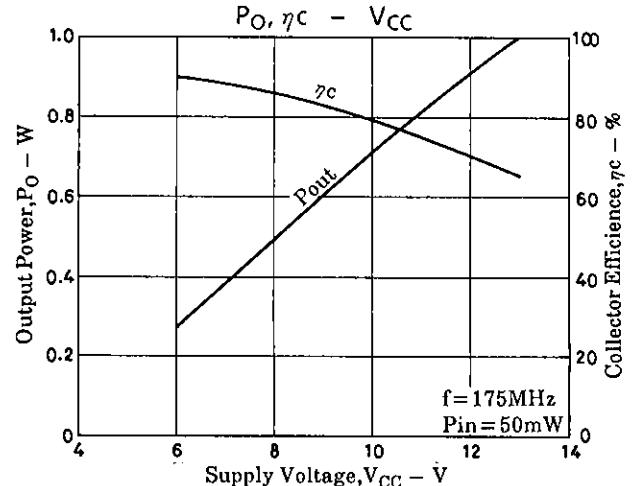
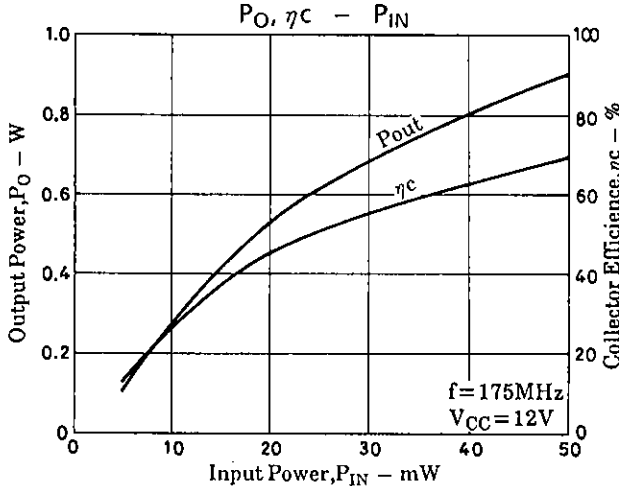
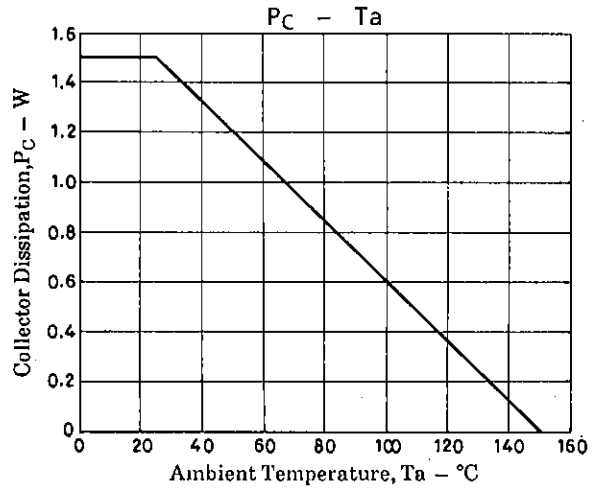
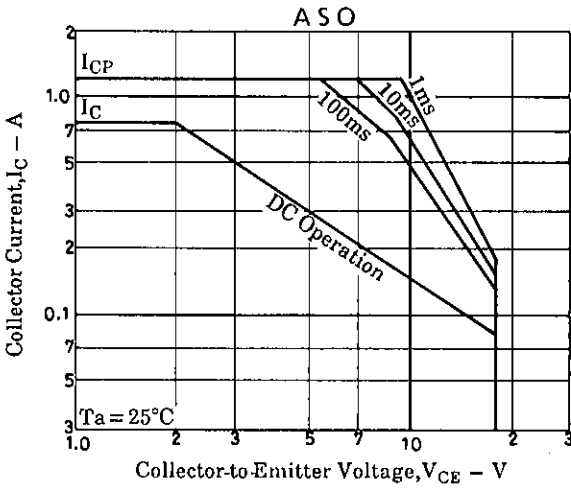
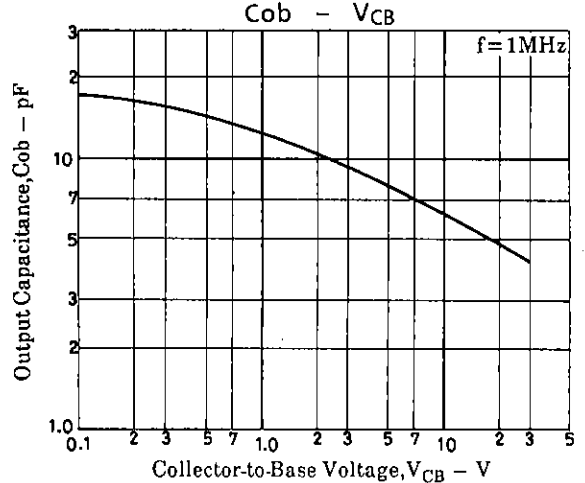
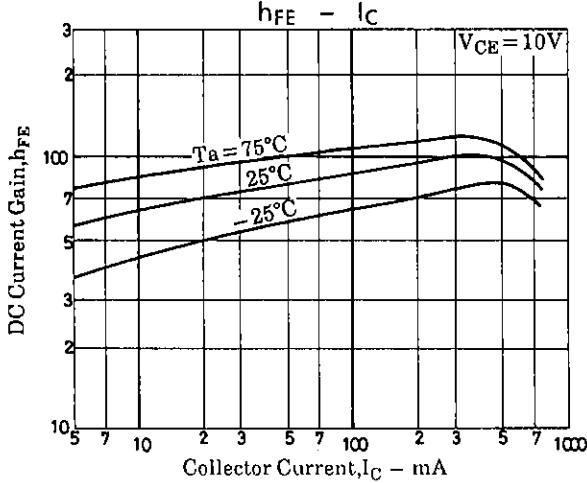
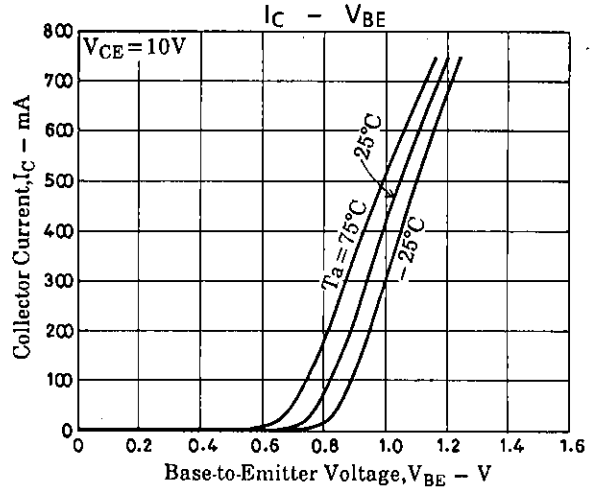
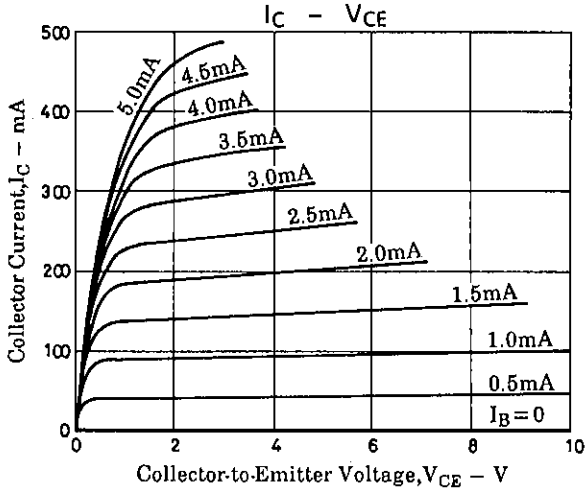
| | | | min | typ | max | unit |
|--------------------------|----------------------|---|-----|-----|-----|------|
| Collector Cutoff Current | I _{CB0} | V _{CB} = 30V, I _E = 0 | | | 50 | μA |
| Emitter Cutoff Current | I _{EBO} | V _{EB} = 2V, I _C = 0 | | | 50 | μA |
| DC Current Gain | h _{FE} | V _{CE} = 10V, I _C = 200mA | 20 | | 200 | |
| C-B Breakdown Voltage | V _{(BR)CB0} | I _C = 100μA, I _E = 0 | 38 | | | V |
| C-E Breakdown Voltage | V _{(BR)CE0} | I _C = 1mA, R _{BE} = ∞ | 18 | | | V |
| E-B Breakdown Voltage | V _{(BR)EBO} | I _E = 100μA, I _C = 0 | 3 | | | V |
| Output Capacitance | C _{ob} | V _{CB} = 10V, f = 1MHz | | 6 | 10 | pF |
| Output Power | P _O | V _{CC} = 12V, f = 175MHz, P _{IN} = 50mW | 0.7 | 0.9 | | W |
| Collector Efficiency | η _c | See specified Test Circuit. | 55 | 70 | | % |

Collector Efficiency Test Circuit



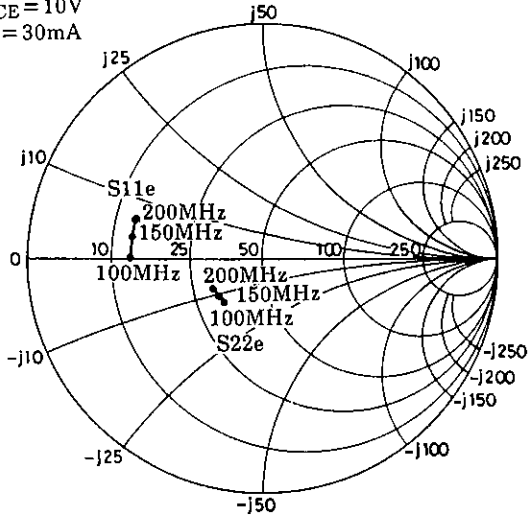
Package Dimensions 2084A
(unit: mm)





S Parameter

$Z_0 = 50\Omega$
 $V_{CE} = 10V$
 $I_C = 30mA$



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